ROITHNER LASERTECHNIK
A-1040 WIEN, FLEISCHMANNGASSE 9
TEL: +43 -1- 586 52 43 FAX: +43 -1- 586 41 43
e-mail: office@roithner-laser.com http://www.roithner-laser.com

RLT80810G TECHNICAL DATA

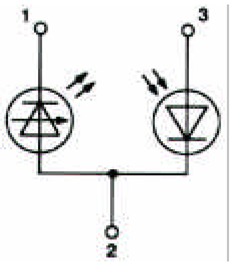
High Power Infrared Laserdiode

Structure: **AlGaAs/GaAs**
Lasing wavelength: **808 +/- 3 nm typ., singlemode**
Typ. optical power: **10 mW**
Package: **9 mm**

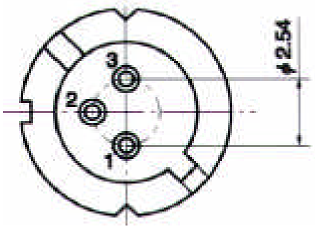
ATTENTION
OBSERVE PRECAUTIONS FOR HANDLING
ELECTROSTATIC SENSITIVE DEVICE

NOTE!
LASERDIODE
MUST BE COOLED!

PIN CONNECTION:



1) Laser diode cathode
2) Laser diode anode and photodiode cathode
3) Photodiode anode



Maximum Ratings (Tc=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Optical Output Power	P_o	12	mW
LD Reverse Voltage	$V_{R(LD)}$	2	V
PD Reverse Voltage	$V_{R(PD)}$	5	V
Operating Temperature	T_C	-40 .. +40	°C
Storage Temperature	T_{STG}	-50 .. +60	°C

Optical-Electrical Characteristics (Tc = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
Threshold Current	I_{th}		25	35	45	mA
Operation Current	I_{op}	$P_o = 10$ mW		60	90	mA
Lasing Wavelength	λ_p	$P_o = 10$ mW	805	808	811	nm
Beam Divergence	$\theta_{//}$	$P_o = 10$ mW		8		°
Beam Divergence	$\theta_{\perp}$	$P_o = 10$ mW		35		°
Differential Efficiency	dP_o/dI_{op}	$P_o = 10$ mW		0.75		mW/mA
Monitor Current	I_m	$P_o = 10$ mW	50	250	300	µA